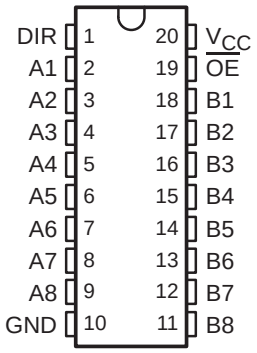
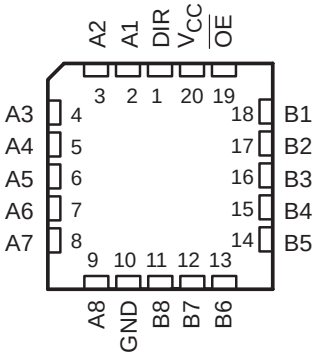
- **State-of-the-Art *EPIC*-II*B*™ BiCMOS Design Significantly Reduces Power Dissipation**
- **Latch-Up Performance Exceeds 500 mA Per JESD 17**
- **Typical V_{OLP} (Output Ground Bounce) < 1 V at V_{CC} = 5 V, T_A = 25°C**
- **I_{off} and Power-Up 3-State Support Hot Insertion**
- **High-Drive Outputs (–32-mA I_{OH}, 64-mA I_{OL})**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW), and Thin Very Small-Outline (DGV) Packages, Ceramic Chip Carriers (FK), Plastic (N) and Ceramic (J) DIPs, and Ceramic Flat (W) Package**

SN54ABTH245 . . . J OR W PACKAGE
SN74ABTH245 . . . DB, DGV, DW, N, OR PW PACKAGE
(TOP VIEW)



SN54ABTH245 . . . FK PACKAGE
(TOP VIEW)



description

These octal bus transceivers are designed for asynchronous communication between data buses. The devices transmit data from the A bus to the B bus or from the B bus to the A bus, depending on the logic level at the direction-control (DIR) input. The output-enable ($\overline{OE}$) input can be used to disable the device so the buses are effectively isolated.

When V_{CC} is between 0 and 2.1 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 2.1 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

This device is fully specified for hot-insertion applications using I_{off} and power-up 3-state. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down. The power-up 3-state circuitry places the outputs in the high-impedance state during power up and power down, which prevents driver conflict.

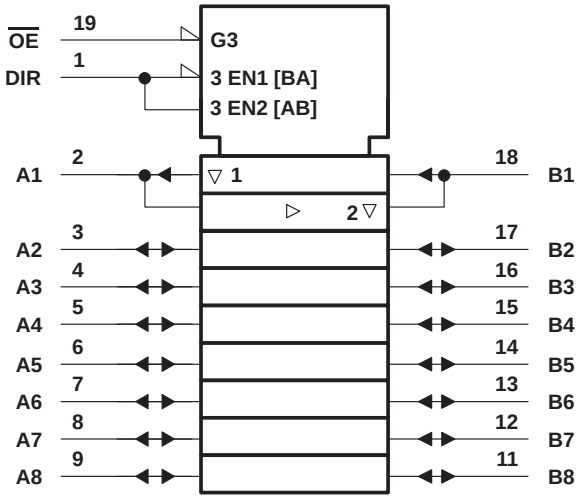
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN54ABTH245 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74ABTH245 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

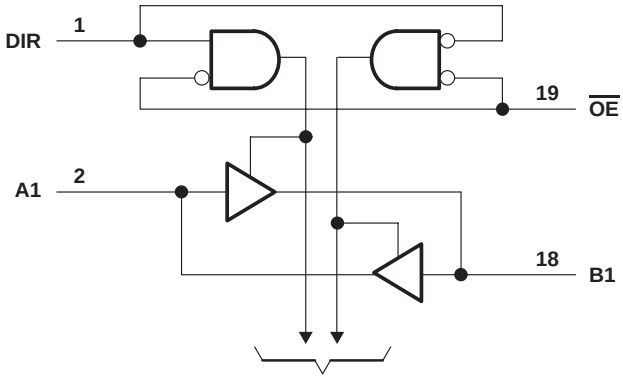
INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 7 V
Input voltage range, V_I (except I/O ports) (see Note 1) . . . . . –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O . . . . . –0.5 V to 5.5 V
Current into any output in the low state, I_O: SN54ABTH245 . . . . . 96 mA
SN74ABTH245 . . . . . 128 mA
Input clamp current, I_{IK} (V_I < 0) . . . . . –18 mA
Output clamp current, I_{OK} (V_O < 0) . . . . . –50 mA
Package thermal impedance, θ_{JA} (see Note 2): DB package . . . . . 70°C/W
DGV package . . . . . 92°C/W
DW package . . . . . 58°C/W
N package . . . . . 69°C/W
PW package . . . . . 83°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 3)

		SN54ABTH245		SN74ABTH245		UNIT
		MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage	4.5	5.5	4.5	5.5	V
V_{IH}	High-level input voltage	2		2		V
V_{IL}	Low-level input voltage		0.8		0.8	V
V_I	Input voltage	0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current		–24		–32	mA
I_{OL}	Low-level output current		48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate		5		5	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate			200		µs/V
T_A	Operating free-air temperature	–55	125	–40	85	°C

NOTE 3: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

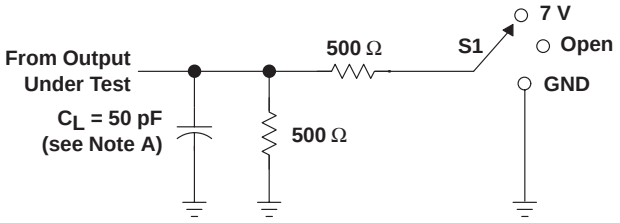
PARAMETER		TEST CONDITIONS		T_A = 25°C			SN54ABTH245		SN74ABTH245		UNIT
				MIN	TYP†	MAX	MIN	MAX	MIN	MAX	
V_{IK}		V_{CC} = 4.5 V,	I_I = –18 mA			–1.2		–1.2		–1.2	V
V_{OH}		V_{CC} = 4.5 V,	I_{OH} = –3 mA	2.5			2.5		2.5		V
		V_{CC} = 5 V,	I_{OH} = –3 mA	3			3		3		
		V_{CC} = 4.5 V	I_{OH} = –24 mA	2			2				
			I_{OH} = –32 mA	2*					2		
V_{OL}		V_{CC} = 4.5 V	I_{OL} = 48 mA			0.55		0.55			V
			I_{OL} = 64 mA			0.55*				0.55	
V_{hys}					100						mV
I_I	Control inputs	V_{CC} = 0 to 5.5 V,	V_I = V_{CC} or GND			±1		±1		±1	µA
	A or B ports	V_{CC} = 2.1 V to 5.5 V,	V_I = V_{CC} or GND			±20		±100		±20	
$I_{I(hold)}$		V_{CC} = 4.5 V	V_I = 0.8 V	100			100		100		µA
			V_I = 2 V	–100			–100		–100		
I_{OZPU}		V_{CC} = 0 to 2.1 V, V_O = 0.5 V to 2.7 V, $\overline{OE}$ = X				±50**		±50**		±50	µA
I_{OZPD}		V_{CC} = 2.1 V to 0, V_O = 0.5 V to 2.7 V, $\overline{OE}$ = X				±50**		±50**		±50	µA
I_{off}		V_{CC} = 0,	V_I or $V_O \le$ 4.5 V			±100				±100	µA
I_{CEX}		V_{CC} = 5.5 V, V_O = 5.5 V	Outputs high			50		50		50	µA
I_O‡		V_{CC} = 5.5 V,	V_O = 2.5 V	–50	–140	–180	–50	–180	–50	–180	mA
I_{CC}	A or B ports	V_{CC} = 5.5 V, I_O = 0, V_I = V_{CC} or GND	Outputs high		5	250		250		250	µA
			Outputs low		22	30		30		30	mA
			Outputs disabled		1	250		250		250	µA
ΔI_{CC}§	Data inputs	V_{CC} = 5.5 V, One input at 3.4 V, Other inputs at V_{CC} or GND	Outputs enabled			1.5		1.5		1.5	mA
			Outputs disabled			1.5		1.5		1.5	mA
	Control inputs	V_{CC} = 5.5 V, One input at 3.4 V, Other inputs at V_{CC} or GND				1.5		1.5		1.5	mA
C_i	Control inputs	V_I = 2.5 V or 0.5 V			4						pF
C_{io}	A or B ports	V_O = 2.5 V or 0.5 V			8						pF

* On products compliant to MIL-PRF-38535, this parameter does not apply.
** On products compliant to MIL-PRF-38535, this parameter is not production tested.
† All typical values are at V_{CC} = 5 V.
‡ Not more than one output should be tested at a time, and the duration of the test should not exceed one second.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

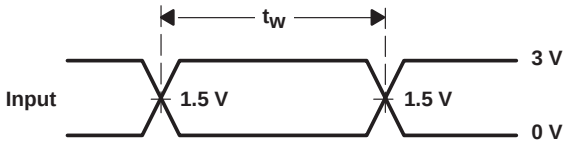
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 5 V, T_A = 25°C			SN54ABTH245		SN74ABTH245		UNIT
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A or B	B or A	1	2	3.2	0.8	3.8	1	3.6	ns
t_{PHL}			1	2.6	3.5	0.8	4.2	1	3.9	
t_{PZH}	$\overline{OE}$	A or B	2	3.5	4.5	1.2	6.2	2	5.6	ns
t_{PZL}			1.9	4	5.3	1.3	7	1.9	6.2	
t_{PHZ}	$\overline{OE}$	A or B	2.2	4.4	5.4	2.2	6.1	2.2	5.9	ns
t_{PLZ}			1.5	3	4	1	4.9	1.5	4.5	
$t_{sk(o)}$					0.5				0.5	ns

PARAMETER MEASUREMENT INFORMATION

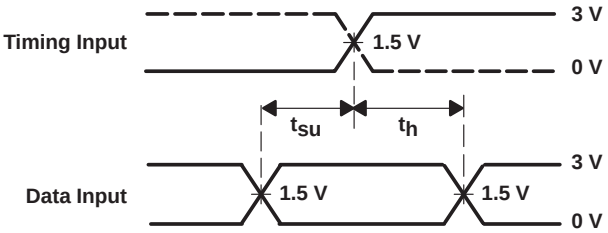


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	7 V
t_{PHZ}/t_{PZH}	Open

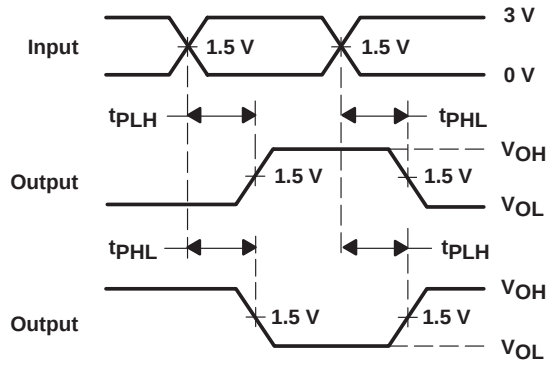
LOAD CIRCUIT



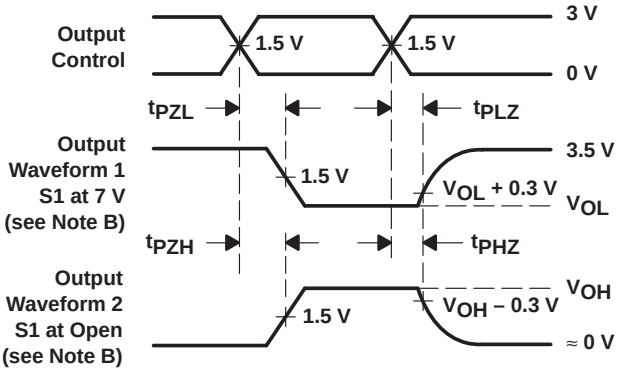
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

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